

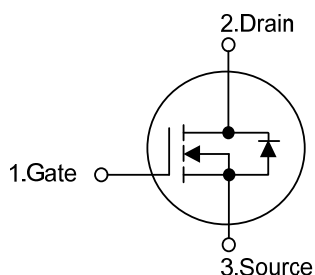
**16N50-TC****Power MOSFET****16A, 500V N-CHANNEL
POWER MOSFET****DESCRIPTION**

The UTC **16N50-TC** are N-Channel enhancement mode power field effect transistors (MOSFET) which are produced using UTC's proprietary, planar stripe, DMOS technology.

These devices are suited for high efficiency switch mode power supply. To minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode the advanced technology has been especially tailored.

FEATURES

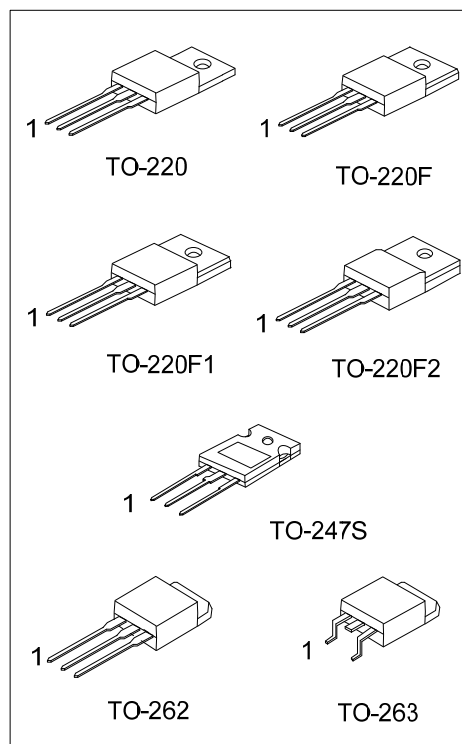
- * $R_{DS(ON)} \leq 0.4 \Omega$ @ $V_{GS}=10V$, $I_D=8.0A$
- * Fast switching capability
- * Avalanche energy specified
- * Improved dv/dt capability, high ruggedness

SYMBOL**ORDERING INFORMATION**

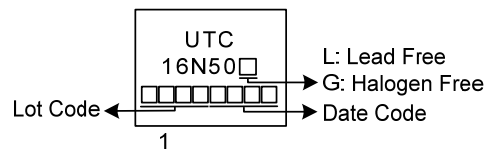
Ordering Number		Package	Pin Assignment			Packing
Lead Free	Halogen Free		1	2	3	
16N50L-TA3-T	16N50G-TA3-T	TO-220	G	D	S	Tube
16N50L-TF1-T	16N50G-TF1-T	TO-220F1	G	D	S	Tube
16N50L-TF2-T	16N50G-TF2-T	TO-220F2	G	D	S	Tube
16N50L-TF3-T	16N50G-TF3-T	TO-220F	G	D	S	Tube
16N50L-T2Q-T	16N50G-T2Q-T	TO-262	G	D	S	Tube
16N50L-T47S-T	16N50G-T47S-T	TO-247S	G	D	S	Tube
16N50L-TQ2-T	16N50G-TQ2-T	TO-263	G	D	S	Tube
16N50L-TQ2-R	16N50G-TQ2-R	TO-263	G	D	S	Tape Reel

Note: Pin Assignment: G: Gate D: Drain S: Source

16N50G-TA3-T (1) Packing Type (2) Package Type (3) Green Package	(1) T: Tube, R: Tape Reel (2) TA3: TO-220, TF1: TO-220F1, TF2: TO-220F2, TF3: TO-220F, T47S: TO-247S, T2Q: TO-262, TQ2: TO-263 (3) G: Halogen Free and Lead Free, L: Lead Free
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■ MARKING



■ **ABSOLUTE MAXIMUM RATINGS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER		SYMBOL	RATINGS	UNIT
Drain-Source Voltage		V_{DSS}	500	V
Gate-Source Voltage		V_{GSS}	± 30	V
Drain Current	Continuous	I_D	16	A
	Pulsed (Note 2)	I_{DM}	32	A
Avalanche Energy	Single Pulsed (Note 3)	E_{AS}	352	mJ
Peak Diode Recovery dv/dt (Note 4)		dv/dt	3.7	V/ns
Power Dissipation	TO-220/TO-262 TO-263	P_D	180	W
	TO-220F/TO-220F1 TO-220F2		41	W
	TO-247S		200	W
Junction Temperature		T_J	+150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55 ~ +150	$^\circ\text{C}$

Notes: 1. Absolute maximum ratings are those values beyond which the device could be permanently damaged.

Absolute maximum ratings are stress ratings only and functional device operation is not implied.

2. Repetitive Rating : Pulse width limited by maximum junction temperature.

3. $L = 10\text{mH}$, $I_{AS} = 8.4\text{A}$, $V_{DD} = 50\text{V}$, $R_G = 25\Omega$, Starting $T_J = 25^\circ\text{C}$

4. $I_{SD} \leq 16\text{A}$, $di/dt \leq 200\text{A/s}$, $V_{DD} \leq BV_{DSS}$ Starting $T_J = 25^\circ\text{C}$

■ **THERMAL DATA**

PARAMETER		SYMBOL	RATINGS	UNIT
Junction to Ambient	TO-220/TO-220F TO-220F1/TO-220F2 TO-262/TO-263	θ_{JA}	62.5	$^\circ\text{C/W}$
	TO-247S		50	$^\circ\text{C/W}$
Junction to Case	TO-220/TO-262 TO-263	θ_{JC}	0.69	$^\circ\text{C/W}$
	TO-220F/TO-220F1 TO-220F2		3.04	$^\circ\text{C/W}$
	TO-247S		0.625	$^\circ\text{C/W}$

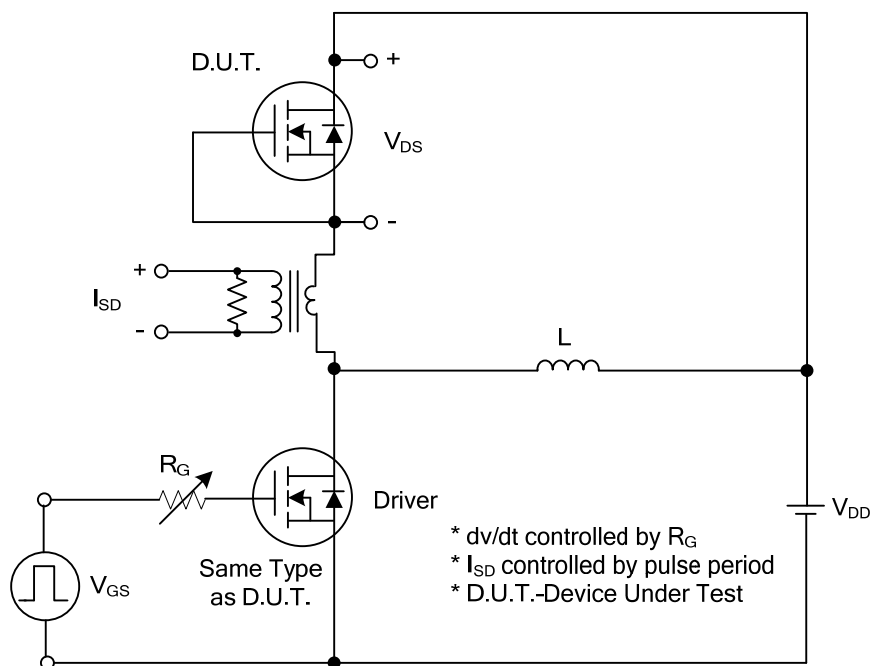
■ **ELECTRICAL CHARACTERISTICS** ($T_C = 25^\circ\text{C}$, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
OFF CHARACTERISTICS						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250μA	500			V
Drain-Source Leakage Current	I _{DSS}	V _{DS} =500V, V _{GS} =0V			10	μA
Gate-Source Leakage Current	I _{GSS}	V _{GS} =±30V, V _{DS} =0V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} =V _{GS} , I _D =250μA	2.0		4.0	V
Static Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =8.0A			0.4	Ω
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{ISS}	V _{DS} =25V, V _{GS} =0V, f=1MHz		1751		pF
Output Capacitance	C _{OSS}			209		pF
Reverse Transfer Capacitance	C _{RSS}			10		pF
SWITCHING CHARACTERISTICS						
Total Gate Charge	Q _G	V _{DS} =400V, V _{GS} =10V, I _D =16A I _G =1mA (Note 1, 2)		38		nC
Gate-Source Charge	Q _{GS}			10		nC
Gate-Drain Charge	Q _{GD}			9		nC
Turn-On Delay Time	t _{D(ON)}	V _{DD} =100V, V _{GS} =10V, I _D =16A, R _G =25Ω (Note 1, 2)		24		ns
Turn-On Rise Time	t _R			20		ns
Turn-Off Delay Time	t _{D(OFF)}			165		ns
Turn-Off Fall Time	t _F			60		ns
SOURCE- DRAIN DIODE RATINGS AND CHARACTERISTICS						
Maximum Body-Diode Continuous Current	I _S				16	A
Maximum Body-Diode Pulsed Current	I _{SM}				32	A
Drain-Source Diode Forward Voltage	V _{SD}	V _{GS} =0V, I _S =16A			1.4	V
Reverse Recovery Time	t _{rr}	V _{GS} =0V, I _S =16A, di/dt=100A/μs		362		ns
Reverse Recovery Charge	Q _{rr}			4.9		μC

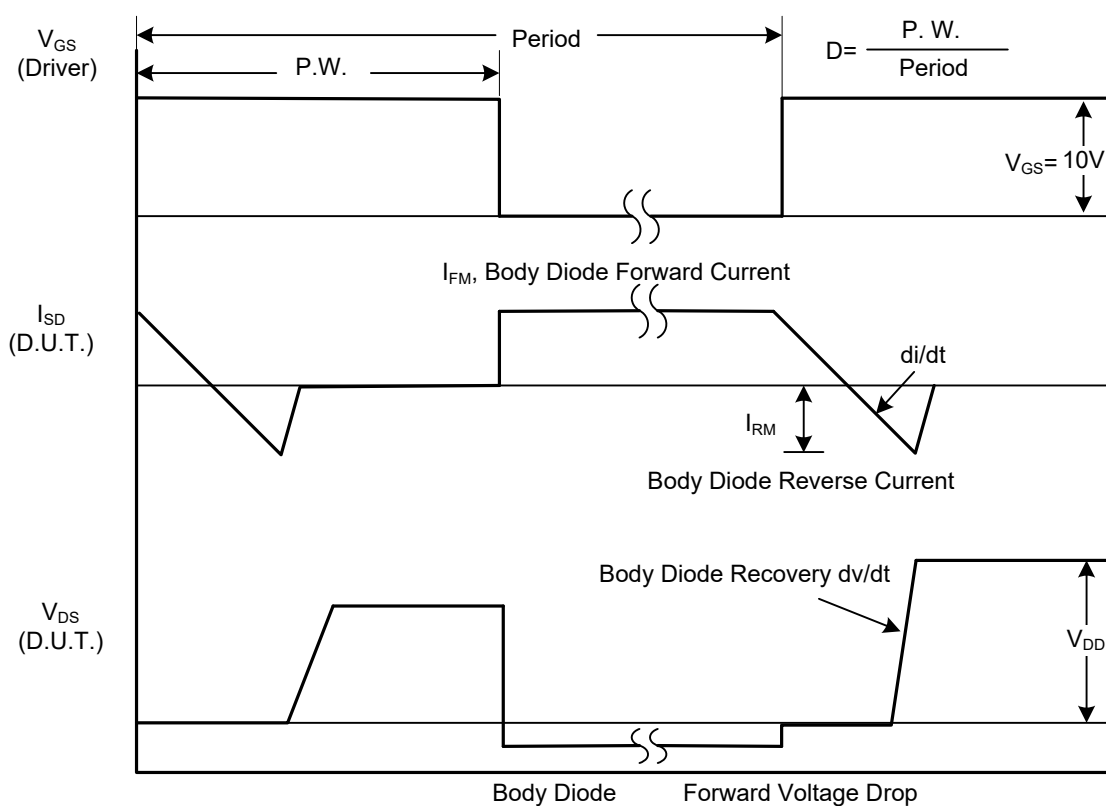
Notes: 1. Pulse Test : Pulse width $\leq 300\mu s$, Duty cycle $\leq 2\%$.

2. Essentially independent of operating temperature.

■ TEST CIRCUITS AND WAVEFORMS

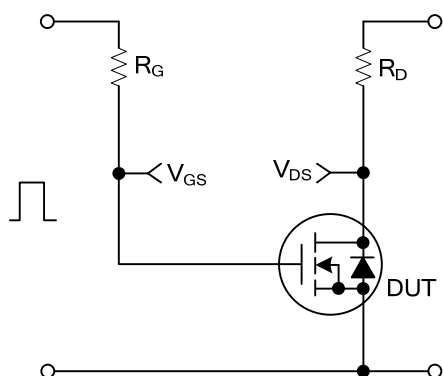


Peak Diode Recovery dv/dt Test Circuit

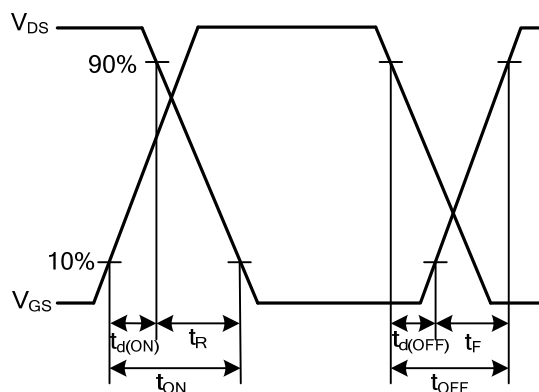


Peak Diode Recovery dv/dt Waveforms

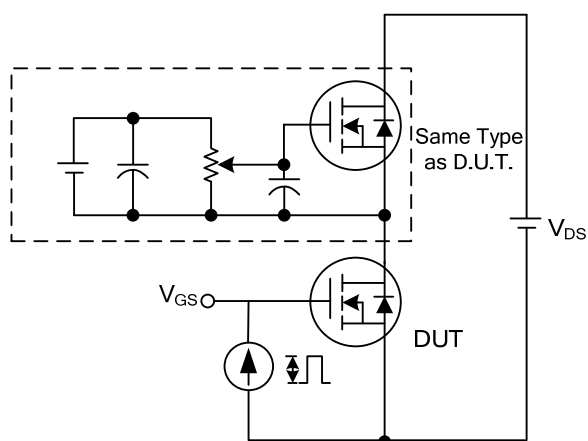
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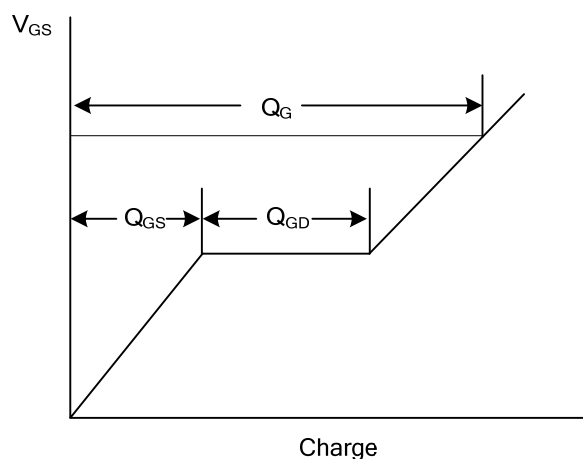
Switching Test Circuit



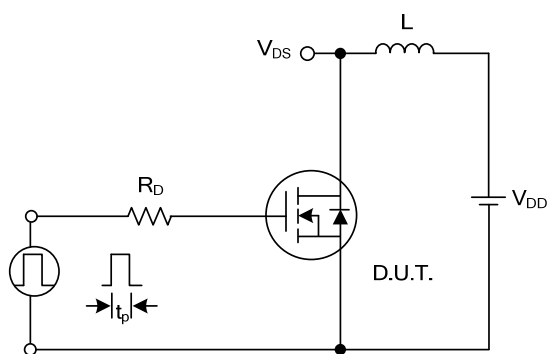
Switching Waveforms



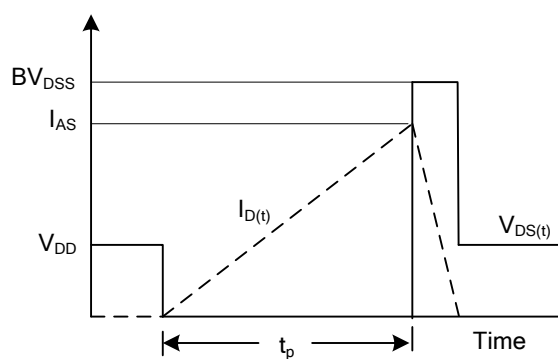
Gate Charge Test Circuit



Gate Charge Waveform

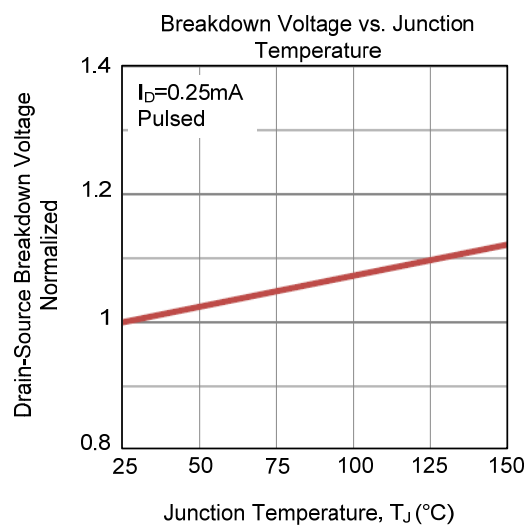
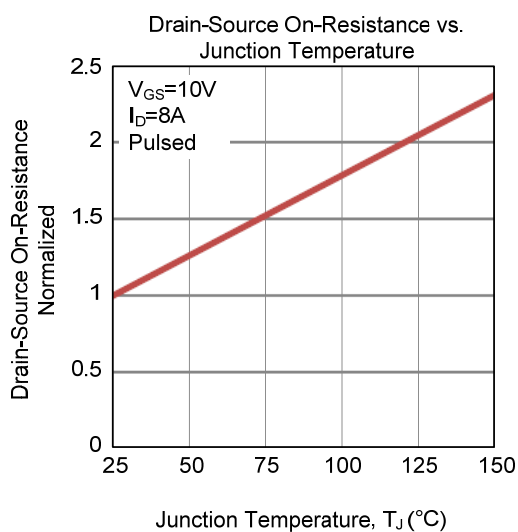
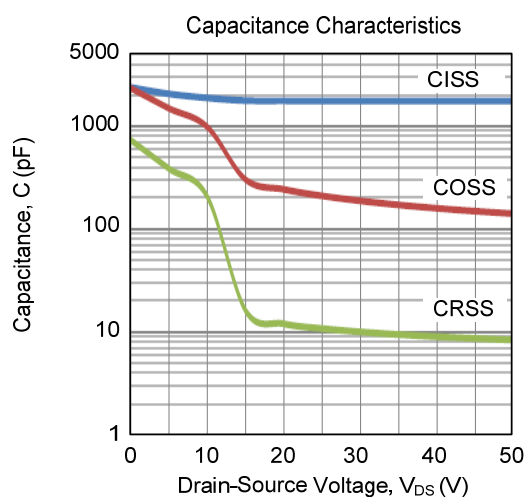
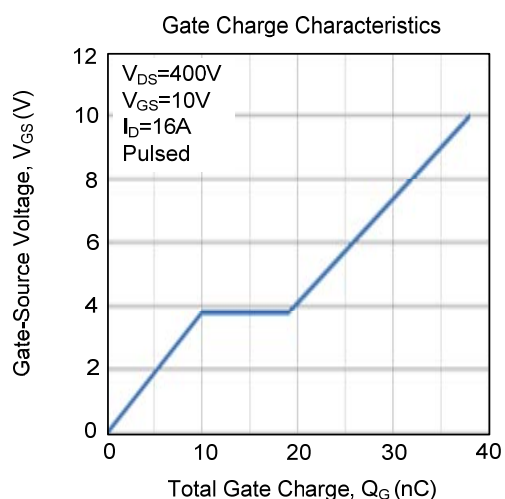
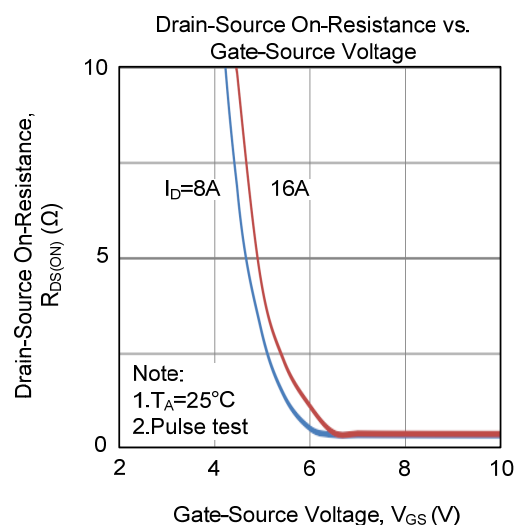
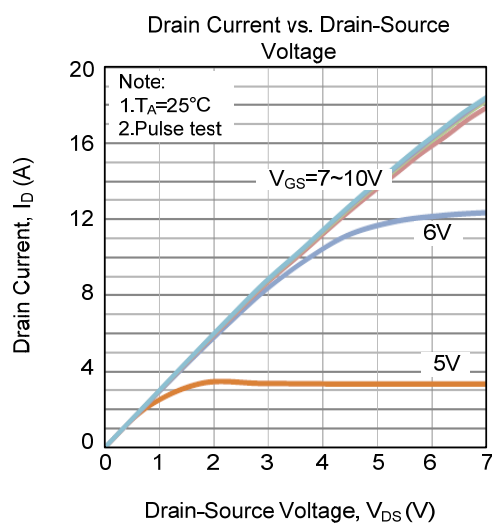


Unclamped Inductive Switching Test Circuit

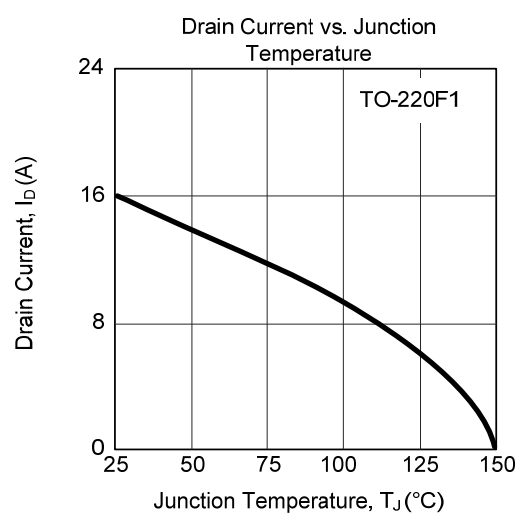
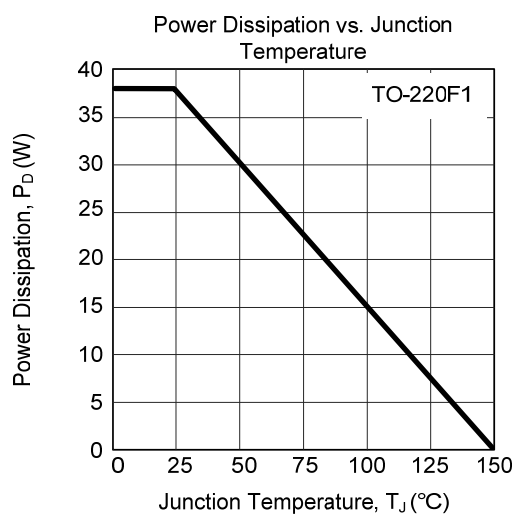
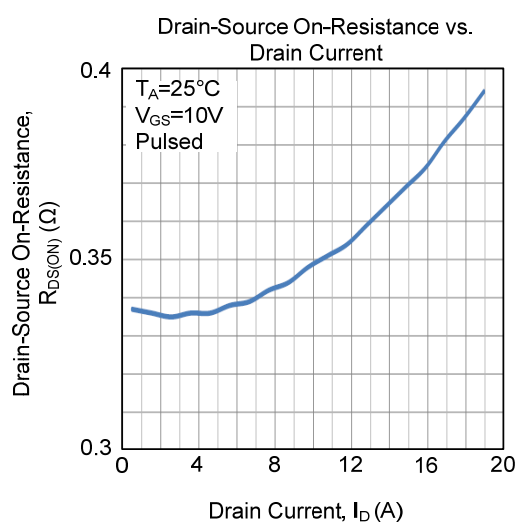
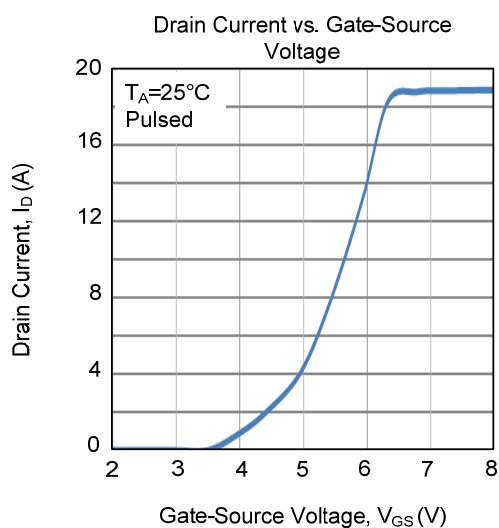
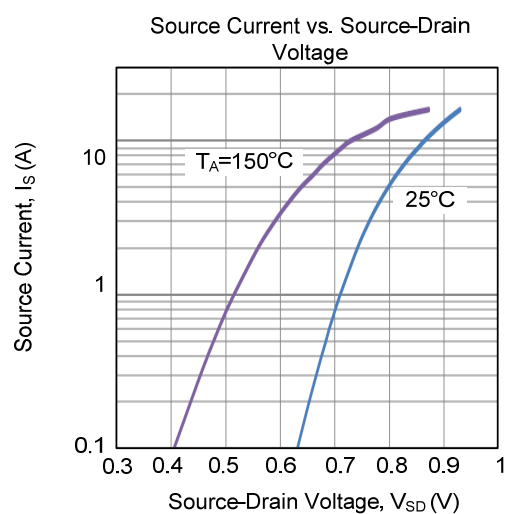
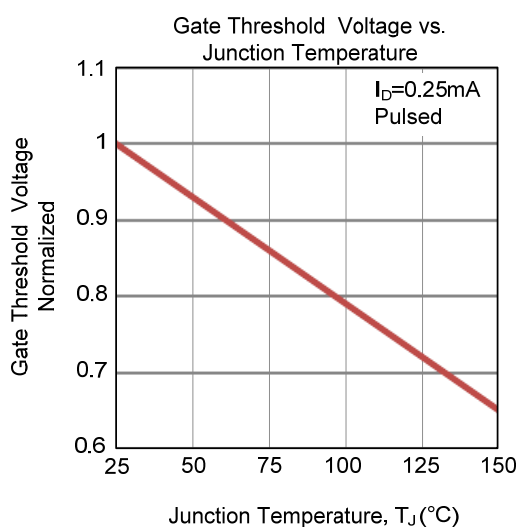


Unclamped Inductive Switching Waveforms

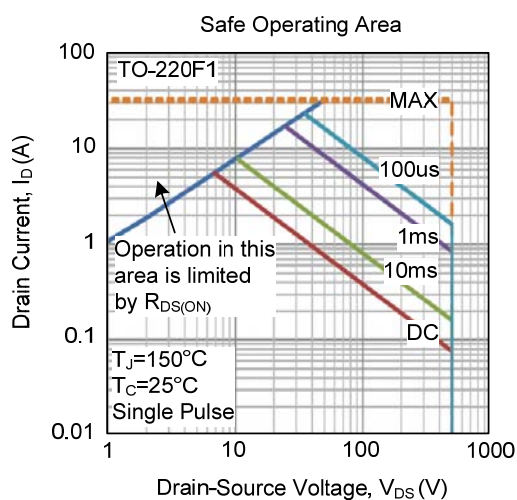
TYPICAL CHARACTERISTICS



■ TYPICAL CHARACTERISTICS (Cont.)



■ TYPICAL CHARACTERISTICS (Cont.)



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